

Abstract Submitted  
for the MAR09 Meeting of  
The American Physical Society

**Diffraction Symmetries in Epitaxially-Grown Graphene and the SiC Substrate** DAVID SIEGEL, UC Berkeley Physics / LBNL Materials Sciences, SHUYUN ZHOU, LBNL Materials Sciences, FARID EL GABALY, Sandia National Laboratory, ANDREAS SCHMID, Lawrence Berkeley National Laboratory, KEVIN MCCARTY, Sandia National Laboratory, ALESSANDRA LANZARA, UC Berkeley Physics / LBNL Materials Sciences — Diffraction patterns in epitaxially-grown graphene and the SiC substrate are studied by observing dark field low energy electron microscopy (LEEM) and low energy electron diffraction (LEED) images. The breaking of 6-fold symmetry is mapped out as a function of the position on the sample for different crystal periodicities. Such observations provide information about the stacking and domain boundaries in epitaxially-grown graphene.

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Date submitted: 19 Nov 2008

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